PTO/SB/08 (09-06)

Approved for use through 03/31/2007. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paper ork Reduction

Sheet

of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control

Substitute for form 1449/PTO
INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

Date Submitted: March 11, 2008

(use as many sheets as necessary)

Complete if Known			
Application Number	10/538,739		
Filing Date	12/15/2003		
First Named Inventor	Yasuhiro OKAMOTO		
Art Unit	2814		
Examiner Name	Sarah Kate Salerno		
Attorney Docket Number	029437-0108		

	U.S. PATENT DOCUMENTS				
Examiner	Cite	Document Number	Publication Date	Name of Patentee or Applicant of	Pages, Columns, Lines, Where Relevant
Initials* No.1	Number-Kind Code <sup>2</sup> (if known)	MM-DD-YYYY	Cited Document	Passages or Relevant Figures Appear	

UNPUBLISHED U.S. PATENT APPLICATION DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Application Document Serial Number-Kind Code <sup>2</sup> (if known)	Filing Date of Cited Document MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

			FOREIGN PATENT	DOCUMENTS		
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3-</sup> Number <sup>4-</sup> Kind Code <sup>5</sup> ( <i>if known</i> )	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Documents	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Te
	B1	JP 2002-359256A	12-13-2002	FUJITSU LTD.		

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T6
	B2	LI et al., "High breakdown voltage GaN HFET with field plate," Electronics Letters, February 1, 2001, Vol. 37, No. 3, pp. 196-197.	
	В3	TAN et al., "The Effect of Dielectric Stress on the Electrical Characteristics of AlGaN/GaN Heterostructure Field-Effect Transistors (HFETs)," The 10 <sup>th</sup> IEEE International Symposium on Electron Devices for Microwave and Optelectronic Applications, November 2002, pp. 130-135.	
	B4	ZHANG,N.Q. et al., "Effects of surface traps on breakdown voltage and switching speed of GaN power switching HEMTs," 2001 IEEE, pp. 25.5.1-25.5.4.	
		·	

Examiner Signature	Date Considered	

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional). 2 See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. 3 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the Emperor must precede the serial number of the patent document. 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. 6 Applicant is to place a check mark here if English language Translation is attached. This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.